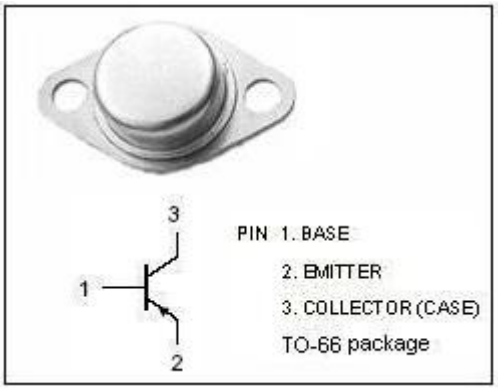
isc Silicon PNP Power Transistor 2SA652

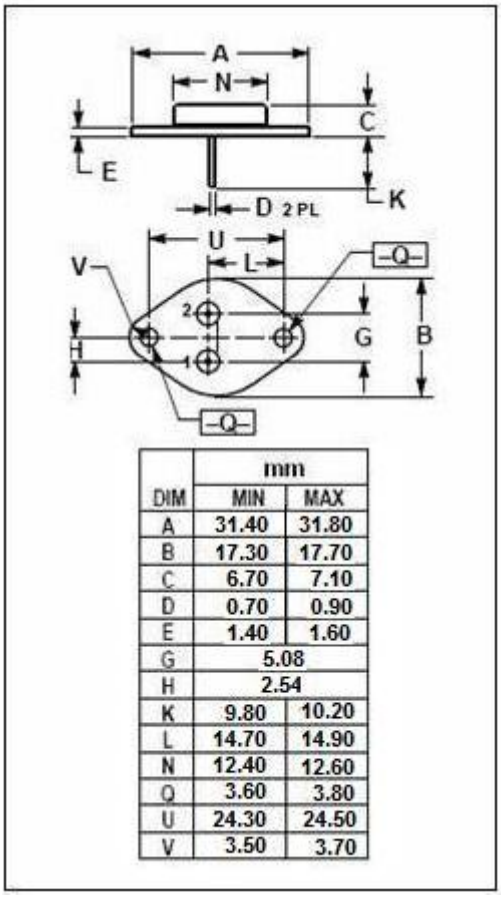


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -100V(Min.)
- Contunuous Collector Current I_C= -1A
- Power DissipationP_C= 15W @T_C= 25℃
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for low frequency power amplifier color TV vertical deflection output applications.



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-1.0	A
P_C	Collector Power Dissipation@T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA ; I_B= 0	-100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -1mA; I_E= 0	-150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -150V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μA
h_{FE}	DC Current Gain	I_C= -0.2A; V_{CE}= -5V	40		200	
C_{OB}	Collector Output Capacitance	I_E=0; V_{CB}= -5V; f= 1MHz		100		pF
f_T	Current-Gain—Bandwidth Product	I_C= -0.1A; V_{CE}= -10V		15		MHz